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TITLE: Electronic Circuit Unit Suitable for
Miniaturization

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1. Field of the Invention

2. Description of the Related Art

Recently, the technique for miniaturizing the circuit parts such as chip parts and transistor has been progressed markedly, and for example, the ultra-small chip resistor and chip capacitor having an apparent size of approximately 0.6×0.3 mm have been used practically.

Therefore, it is possible that such small-size chip parts and transistor are used for the above-mentioned conventional electronic circuit unit and are mounted on a substrate with narrow pitch between circuit parts to thereby miniaturize the electronic circuit unit to a certain extent. However, the miniaturization of the circuit parts such as chip parts and transistor is limited, and narrowing of the pitch between parts is limited because many circuit parts should be mounted on a substrate so that soldered portions of individual circuit parts are prevented from short-circuiting. These limitations have prevented further miniaturization of the electronic circuit unit.

Furthermore, in the case in which an electronic circuit unit of this type has, for example, an amplifier circuit and the emitter of a transistor for the amplifier circuit is grounded through a capacitor, a chip capacitor is soldered between a soldering land of a conducting pattern connected to an emitter electrode and a soldering land of a conducting pattern connected to a ground electrode in the above-mentioned conventional art. However, because the inductance of these two conducting patterns is not negligible, grounding is not sufficient and the interaction between the conducting pattern and chip capacitor causes parasitic oscillation disadvantageously.

The present invention has been accomplished in view of the above-mentioned problem of the conventional art,

and it is the object of the present invention to provide a surface mounting type electronic circuit unit that is used suitably for miniaturization without parasitic oscillation.

SUMMARY OF THE INVENTION

The present invention has been accomplished to achieve the above-mentioned object, and an electronic circuit unit of the present invention is characterized in that thin film circuit elements including capacitors, resistors, and inductance elements, and thin film conducting patterns connected to these circuit elements are formed on an alumina substrate, a semiconductor bare chip is mounted on the alumina substrate and the semiconductor bare chip is fixed to the conducting pattern by means of wire bonding, wherein at least one of the capacitors is formed non-rectangular having rectangles projected from one side of another rectangle.

According to the above-mentioned structure, because circuit elements including capacitors, resistors, and inductance elements are formed with high precision by means of thin film forming technique and a semiconductor bare chip is fixed by means of wire bonding, necessary circuit parts are mounted in high density on an alumina substrate and a surface mounting type electronic circuit unit that is suitable for miniaturization is realized. Furthermore, because, of the thin film circuit elements formed on the

alumina substrate, at least one of the capacitors is formed non-rectangular having rectangles projected from one side of another rectangle, the capacitor having a desired capacitance value can be mounted in high density within a limited space on the alumina substrate, and the electronic circuit unit can be further miniaturized.

In the above-mentioned structure, the non-rectangular shape of the capacitor desirably has two or more rectangles that are combined together, and the limited space on the alumina substrate can be used thereby more effectively.

Furthermore, in the above-mentioned structure, the non-rectangular capacitor is desirably an earth capacitor, and an earth capacitor having a relatively large capacitance can be mounted within a space on the alumina substrate in high density by using the non-rectangular capacitor as the earth capacitor.

An electronic circuit unit of the present invention comprises thin film circuit elements including conducting patterns formed on an alumina substrate, a plurality of thin film capacitors formed on the alumina substrate so as to be connected to the conducting patterns, resistors, and inductance elements and a semiconductor bare chip of the transistor wire-bonded to the conducting patterns, wherein the conducting pattern has a connection land connected to the electrode of the transistor to be grounded in the high frequency band, the capacitor has a plurality

of ground capacitors grounded in the high frequency band, and the one electrode of each of the plurality of capacitors is connected to the ground conducting pattern and the other electrode of each of the plurality of capacitors is connected to the connection land through the conducting patterns that are separated from each other.

According to the above-mentioned structure, because circuit elements including capacitors, resistors, and inductance elements are formed with high precision by means of thin film forming technique and a semiconductor bare chip of a transistor is fixed by means of wire bonding, necessary circuit parts are mounted in high density on an alumina substrate and a surface mounting type electronic circuit unit that is suitable for miniaturization is realized. Furthermore, the conducting pattern has a connection land connected to an electrode of the transistor, the one electrode of each of a plurality of ground capacitors is connected to the ground conducting pattern, and the other electrode of each of the plurality of ground capacitors is connected to a connection land through the conducting pattern that are separated from each other. Thereby, the inductance of the whole conducting pattern for connecting ground capacitors is reduced, and the grounding effect of the connection land brought about by the ground capacitor is improved. Furthermore, because the frequency of parasitic oscillation caused from interaction between the ground capacitors and conducting

patterns becomes high, oscillation at the frequency other than the predetermined oscillation frequency is prevented without parasitic oscillation by setting the parasitic oscillation frequency to a value equal to or higher than the operating point frequency of the transistor.

In the above-mentioned structure, it is desirable that the ground capacitors are different from each other in size, the freedom of the conducting pattern layout is thereby extended, and the miniaturization of the electronic circuit unit is more easily realized.

Furthermore, in the above-mentioned structure, it is desirable that a part of the ground conducting pattern is served as the one electrode of each of the ground capacitors, and such structure allows the electronic circuit unit to be further miniaturized.

BRIEF DESCRIPTION OF THE DRAWINGS

FIG. 1 is a perspective view of an electronic circuit unit in accordance with an embodiment of the present invention.

FIG. 2 is a plan view of an alumina substrate illustrating the circuit structure layout.

FIG. 3 is a backside view of the alumina substrate.

FIG. 4 is an explanatory view of the circuit structure.

FIG. 5 is a perspective view illustrating end side electrodes.

FIG. 6 is a cross sectional view of an end side electrode.

FIG. 7A and FIG. 7B are explanatory views illustrating the relation between a semiconductor bare chip and a connection land.

FIG. 8A to FIG. 8J are explanatory views illustrating fabrication process of the electronic circuit unit.

FIG. 9 is an explanatory view of another circuit structure.

FIG. 10 is a plan view of an alumina substrate illustrating another circuit structure layout.

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS

Embodiments of the present invention will be described in detail hereinafter with reference to the drawings. FIG. 1 is a perspective view of an electronic circuit unit, FIG. 2 is a plan view of an alumina substrate illustrating the circuit structure layout, FIG. 3 is a backside view of the alumina substrate, FIG. 4 is an explanatory view of the circuit structure, FIG. 5 is a perspective view illustrating end side electrodes, FIG. 6 is a cross sectional view of an end side electrode, FIG. 7A and FIG. 7B is an explanatory view illustrating the relation between a semiconductor bare chip and a connection land, and FIG. 8A to FIG. 8J is an explanatory view illustrating a fabrication process of an electronic circuit unit.

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The present embodiment is an example in which the present invention is applied to a frequency tuning type booster amplifier, the frequency tuning type booster amplifier is used for improving the reception performance (particularly for improvement of the reception sensitivity and anti-disturbance characteristic) of a portable type television apparatus in combination with UHF tuner. Thereby, a TV signal of a desired frequency is selected, and the selected TV signal is amplified and supplied to the UHF tuner.

FIG. 1 shows an apparent configuration of such frequency tuning type booster amplifier (electronic circuit unit). As shown in FIG. 1, the frequency tuning type booster amplifier comprises an alumina substrate 1 on which circuit component elements are mounted, that will be described hereinafter, and a shield cover 2 fixed to the alumina substrate 1. The frequency tuning type booster amplifier will be used as a surface mounting parts that is to be soldered to a mother substrate not shown in the drawing. The alumina substrate 1 is configured in a rectangular flat plate, which is obtained by cutting a large substrate into divided rectangles and by dividing a divided rectangle further into small pieces. The shield cover 2 is formed by bending a metal plate into a box, and the circuit component element on the alumina substrate 1 is covered by the shield cover 2.

As shown in FIG. 2, the circuit component elements

and a conducting pattern that is served to connect the circuit component elements are provided on the surface of the alumina substrate 1, and as shown in FIG. 3, a conducting pattern that is served as a backside electrode is provided on the backside of the alumina substrate 1. The frequency tuning type booster amplifier in accordance with the present embodiment having the circuit structure as shown in FIG. 4 is provided with a tuning circuit and amplifier circuit for selecting a TV signal and amplification respectively, and the same characters of the circuit diagram shown in FIG. 4 are given to the same circuit component elements shown in FIG. 2. However, FIG. 4 shows only an example of the circuit structure, and the present invention is applied to other electronic circuit units having the circuit structure different from the above-mentioned circuit structure.

As shown in FIG. 4, the frequency tuning type booster amplifier has capacitors C1 to C7, resistors R1 to R3, inductance elements L1 to L3, a diode D1, a transistor Tr1, and conducting paths S1 and S2 that are served as the circuit component element of the tuning circuit and amplifier circuit, and these circuit component elements and the conducting pattern are provided on the surface of the alumina substrate 1. The conducting pattern is formed of, for example, Cr or Cu by means of thin film forming technique such as sputtering, and is shown with hatching having a character P in FIG. 2.

The circuit structure of the frequency tuning type booster amplifier will be described briefly hereunder. The frequency tuning type booster amplifier is provided with the tuning circuit comprising inductance elements L2 and L3, capacitors C3 and C4, and the diode D1 and the amplifier circuit comprising the transistor Tr1, peripheral circuit elements (resistors R1 to R3, capacitor C6), and an unbalance/balance conversion element T to select and amplify a TV signal of a desired frequency. The TV signal of a plurality of frequencies is supplied to the tuning circuit through the capacitor C1. The tuning frequency (resonance frequency) of the tuning circuit is variable by controlling a voltage (Vct1) applied on the cathode of the diode D1, only the desired TV signal is selected by adjusting the tuning frequency to the frequency of the desired TV signal, and the TV signal is supplied to the base of the transistor Tr1 of the amplifier circuit through the capacitor C5. Bias voltages are applied to base bias voltage dividing resistances R1 and R2 of the base of the transistor Tr1, and the collector current (\div emitter current) of the transistor Tr1 is set depending on the resistance value of the emitter resistance R3. The TV signal that has been amplified by means of the transistor Tr1 is sent out from the collector where the unbalance/balance conversion element T is provided. The unbalance/balance conversion element T has an inductance element comprising a pair of conducting paths S1 and S2

that are combined together. The balance TV signal is generated from both ends of the conducting path S2, and supplied to the above-mentioned UHF tuner.

As shown in FIG. 2, ground electrodes (GND) and input electrodes (Vcc, Vctl, and RFin) and output electrodes (RFout) are formed on the ends of the alumina substrate 1, the conducting pattern P is partially served as these electrodes. The ground electrodes, input electrodes, and output electrodes are formed only on two longer sides of the rectangular alumina substrate 1 that are facing each other and are not formed on the two shorter sides that are facing each other. In detail, GND electrodes are formed on both corners of one longer side of the alumina substrate 1, and a Vcc electrode, an RFin electrode, and a Vctl electrode are formed between these GND electrodes. Three GND electrodes are formed on both corners of the other longer side of the alumina substrate 1 and near one corner, and two RFout electrodes are formed between these GND electrodes. As described hereinafter, the two longer sides of the alumina substrate 1 correspond to the parting line used when a large substrate is cut into divided rectangles, and the two shorter sides of the alumina substrate 1 correspond to the parting line used when a divided rectangle is further divided into small pieces.

On the other hand, as shown in FIG. 3, the conducting pattern P1 (backside electrode) formed on the back side of the alumina substrate 1 is facing to the ground electrodes

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(GND), input electrodes (Vcc, Vctl, and RFin), and output electrodes (RFout), and corresponding electrodes are rendered conductive through side end electrodes 3 as shown in FIG. 5 and FIG. 6. An end electrode 3 is formed by plating an Ni underplating layer and an Au layer successively on an Ag thick-film layer. The undermost thick film Ag layer has been formed by forming a thick film of Ag paste containing no glass composition and then by sintering it at a temperature of approximately 200 °C. Therefore, the undermost thick film Ag layer is formed of low temperature sintered material. The Ni underplating layer laminated in-between is served for firm adhering of the Au plating layer, and the uppermost Au plating layer is served for preventing deposition of Ag of the undermost layer on solder when the end side electrode 3 is soldered to a soldering land of a mother substrate not shown in the drawing. In the completed product of the electronic circuit unit formed by mounting the shield cover 2 on the alumina substrate 1, legs 2a formed by bending the shield cover 2 on the side are soldered to the end side electrodes 3 that are conductive to the ground electrodes (GND), and the shield cover 2 is grounded at the four corners of the alumina substrate 1.

Each of the capacitors C1 to C7 among the above-mentioned circuit component elements is formed by laminating a top electrode on a bottom electrode with interposition of a film of dielectric material such as

SiO_2 , and these thin films are formed by means of sputtering. A Cu layer is formed on the surface of the top electrode and the Cu layer is effective to improve Q of the resonance circuit. The top electrode and the bottom electrode of each of the capacitors C1 to C7 is connected to the conducting pattern P, and discharging neighboring gaps (air gap) G are formed between the capacitor C7 and the Vcc electrode on the conducting pattern P, between the capacitor C7 and the RFout electrode on the conducting pattern P, and between the capacitor C2 and the Vctl electrode on the conducting pattern P. Each of these neighboring gaps G is formed of a pair of projections provided on the parallel conducting patterns P facing each other, and the tips of both projections are facing each other with interposition of a certain gap. In this case, the dimensional precision of the conducting pattern P and the GND electrode is very high because of the thin film forming technique, the gap dimensional size of the neighboring gap can be made very small, and discharging can occur at a low voltage. Among the capacitors C1 to C7, the capacitors C1 and C3 to C5 are formed simply rectangular, but the capacitors C2 and C7 are formed complexly non-rectangular with combination of two or more rectangles. In detail, the capacitor C2 has a convex shape having two rectangles projected from one side of another rectangle, and the capacitor C7 has a shape formed by three rectangles that are located continuously with a deviation

in the longitudinal direction successively. These capacitors C2 and C7 are served as the ground capacitor for which a relatively large capacitance value is required, the ground capacitors C2 and C7 are formed complexly non-rectangular as described hereinabove because the limited space on the alumina substrate 1 is effectively used, and the capacitor of a desired capacitance value can be mounted in high density.

Furthermore, among the capacitors C1 to C7, the capacitor C6 comprises two ground capacitors having difference capacitance values, and the two capacitors are connected in parallel with interposition of a pair of conducting pattern P that are separated each other. In detail, as shown in FIG. 2, one electrode of each of both ground capacitors C6 is connected to the ground conducting pattern P connected to the GND electrode, and the other electrode of each of both ground capacitors C6 is connected to a connection land SL of the transistor Tr1 with interposition of the two conducting patterns P that are separated each other. As it is obvious from FIG. 4, the capacitor C6 is located between the emitter of the transistor Tr1 and the ground, and the above-mentioned connection land SL is the portion where the emitter electrode of the transistor Tr1 is subjected to wire bonding. Therefore, the capacitance value of the capacitor C6 is set by two ground capacitors connected in parallel with interposition of the conducting patterns P that are

separated each other. As the result, the inductance of the whole conducting patterns P extending from the emitter electrode of the transistor Tr1 to the ground with interposition of the capacitor C6 is reduced, and the grounding effect of the connection land SL that is brought about by means of the ground capacitor C6 is improved. Furthermore, the parasitic oscillation frequency due to the ground capacitors C6 and conducting patterns P becomes higher. Therefore, the parasitic oscillation is prevented by setting the frequency to a value equal to or higher than the operating point frequency of the transistor Tr1.

The resistors R1 to R3 are resistance films formed of, for example, TaSiO₂ by means of thin film forming technique such as sputtering, and a film of dielectric material such as SiO₂ is formed on the surface of a resistor as required. As shown in FIG. 2, the resistors R1 and R2 among the three film resistors R1 to R3 are located adjacently in parallel each other on the alumina substrate 1, and the other film resistor R3 is located apart from the resistors R1 and R2. Because the film resistors R1 and R2 are formed adjacently, the ratio of the whole dispersion of the resistors R1 and R2 can be equalized even though the resistance value of the resistors R1 and R2 deviates from the desired value. As it is obvious from FIG. 4, the resistors R1 and R2 are served as the base bias voltage dividing resistor, a voltage of

means of thin film forming technique such as sputtering, and connected to the conducting pattern P. A Cu layer is formed on each of the inductance elements L1 to L3, and the Cu layer is effective to increase Q of a resonance circuit. Each of the inductance elements L1 and L2 is formed rectangularly swirlingly, and one end of each of the inductance elements L1 and L2 is wire-bonded to the Vctl electrode or ground conducting pattern P. The inductance element L2 is served to roughly set the resonance frequency, and the inductance element L3 is connected to the other end of the inductance element L2. The inductance element L3 is an adjusting conducting pattern served to adjust the resonance frequency. The inductance element L3 is trimmed as shown in FIG. 2 with a broken line to thereby increase the number of turns of the inductance element L2, and as the result the resonance frequency is adjusted. In this case, if the conductor width of the trimmed inductance element L3 is equalized to the conductor width of the inductance element L2 that is served for setting the resonance frequency, the characteristic impedance of the inductance element L2 is resultantly equalized to the characteristic impedance of the inductance element L3.

As described hereinbefore, the unbalance/balance conversion element T has the inductance element comprising the pair of conducting paths S1 and S2 combined each other, and these thin film conducting paths S1 and S2 are formed on the alumina substrate 1. These conducting paths S1

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such as cream solder or conductive paste, and the other electrode disposed on the top surface of the semiconductor bare chip is connected to the predetermined position on the conducting pattern P by means of wire bonding. Furthermore, the semiconductor bare chip of the transistor Tr1 is formed also rectangular, the collector electrode disposed on the bottom surface of the semiconductor bare chip is fixed to the connection land by use of conductive adhesive, and the base electrode and the emitter electrode are connected to the predetermined position on the conducting pattern P by means of wire bonding. As in the case of the above-mentioned end side electrode 3, an Ni underplating layer and an Au plating layer are laminated successively on each of these connection lands. Herein, as shown in FIG. 7A and FIG. 7B, the connection land 5 is formed so that the area of the connection land 5 is smaller than the bottom surface area of the semiconductor bare chip 4, a space for retaining conductive adhesive is secured under the semiconductor bare chip 4 because of such structure. As the result, the space does not allow conductive adhesive from spewing outside the semiconductor bare chip 4 to result in short-circuit to the surrounding conducting pattern P. Furthermore, an opening 5a is formed in the connection land 5 and excessive conducting adhesive is retained in the opening 5a. Therefore, spewing of conductive adhesive is prevented surely the more.

Next, the fabrication process of an electronic

circuit unit structured as described hereinabove will be described mainly with reference to FIG. 8A to FIG. 8J.

At first, as shown in FIG. 8A, a TaSiO₂ film is formed on the entire surface of an alumina substrate 1 by means of sputtering and then etched in desired configuration to form a resistance film 6. Thereby, portions corresponding to the resistors R1 to R3 are formed. Next, as shown in FIG. 8B, Cr film or Cu film is formed on the resistance film 6 by means of sputtering and then etched in desired configuration to form the bottom electrode 7. Then, as shown in FIG. 8C, a SiO₂ film is formed on the bottom electrode 7 by means of sputtering and then etched in desired configuration to form the dielectric film 8. Next, as shown in FIG. 8D, a Cr film or Cu film is formed on the dielectric film 8 by means of sputtering and then etched in desired configuration to form the top electrode 9. As the result, the area corresponding to the conducting pattern P, inductance elements L1 to L3, and conducting paths S1 and S2 is formed by the bottom electrode 7 or the top electrode 9, and the area corresponding to the capacitors C1 to C7 is formed by the laminate comprising the bottom electrode 7, dielectric film 8, and top electrode 9. Next, a Cu layer is formed on the surface of the area corresponding to the inductance elements L1 to L3, conducting paths S1 and S2, and capacitors C1 to C7 by means of plating or thin film forming technique, and a protecting film 10 is formed on the area excluding the

area of the conducting pattern P as shown in FIG. 8E. Next, as shown in FIG. 8F, a Cr film or Cu film is formed on the entire back surface of the alumina substrate 1 by means of sputtering, and then etched in desired configuration to form the backside electrode 11. Thereby, the area corresponding to the backside conducting pattern P1 is formed.

Steps described with reference to FIG. 8A to FIG. 8F are carried out on a large substrate consisting of alumina material on which notch grooves extending in vertical direction and horizontal direction in lattice fashion are formed. On the other hand, steps described with reference to FIG. 8G to FIG. 8J are carried out on each divided rectangular piece obtained by cutting along notch grooves extending in one direction.

In detail, the large substrate is cut into divided rectangular pieces, thick film Ag layers 12 are formed on both end sides of the alumina substrate 1, which are cut surfaces of the divided piece as shown in FIG. 8G, and the ground electrodes (GND), input electrodes (Vcc, Vctl, and RFin), and output electrodes (RFout) of the conducting patterns P and P1 disposed on both front and back surface of the alumina substrate 1 are connected conductively with the Ag layers 12. The Ag layer 12 corresponds to the Ag thick-film layer of the end side electrode 3, which is formed of low temperature sintered material consisting of Ag paste including no glass

composition. The thick film forming step for forming the Ag layer 12 can be carried out on one rectangular divided piece. However otherwise, the step may be carried out on a plurality of divided pieces that are stacked with interposition of a small space between adjacent pieces, and as the result the thick film Ag layer 12 is formed on a plurality of divided pieces simultaneously. This method is suitable for mass-production. Next, Ni under layer and Au layer are formed successively by means of plating on the Ag layer 12 and the surfaces of the connection lands where the semiconductor bare chip is to be mounted. Thereafter as shown in FIG. 8H, the semiconductor bare chip of the diode D1 and transistor Tr1 is fixed on the connection lands by use of conductive adhesive such as cream solder or conductive paste. In this case, because the area of the connection land is smaller than the bottom surface area of the semiconductor bare chip as described hereinabove, spewing of conductive adhesive from the semiconductor bare chip is prevented, and as the result undesired short-circuit between the conductive adhesive and the conducting pattern P that is surrounding the semiconductor bare chip is prevented. Next, as shown in FIG. 8I, each semiconductor bare chip is fixed to the predetermined position of the conducting pattern P by means of wire bonding. Thereafter as shown in FIG. 8J, the resistor R3 that is served as the emitter resistance is trimmed to adjust the output and the inductance element

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L3 that is served as the adjusting conducting pattern is trimmed to adjust the resonance frequency. In this case, adjusting of the resonance frequency is carried out on a rectangular divided piece that has not been divided into individual alumina substrate 1, and the ground electrodes (GND) are provided on corners of each alumina substrate 1. Therefore, ground electrodes (GND) are located always between input electrodes (Vcc, Vctl, and RFin) and output electrodes (RFout) located on adjacent alumina substrates 1, and as the result the adjustment of resonance frequency will not adversely affect the circuit of the adjacent alumina substrate 1.

Next, a shield cover 2 is fixed to each rectangular divided alumina substrate 1 and legs 2a of the shield cover 2 are soldered to the end side electrodes 3 that are connected to the ground electrodes (GND). Thereafter, the divided piece is cut along the dividing grooves extending in the other direction to form individual alumina substrates 1, and an electronic circuit as shown in FIG. 1 is thus obtained.

According to the electronic circuit unit in accordance with the above-mentioned embodiment having the structure as described hereinbefore, thin film circuit elements such as the capacitors C1 to C7, resistors R1 to R3, inductance elements L1 to L3, and conducting paths S1 and S2 and a thin film conducting pattern P that is connected to these circuit elements are formed on the

alumina substrate 1, the semiconductor bare chip of the diode D1 and transistor Tr1 is fixed on the alumina substrate 1 by means of wire bonding, and end side electrodes 3 that is connected to ground electrodes and input/output electrodes of the conducting pattern are formed on the side surface of the alumina substrate 1. As the result, necessary circuit component elements can be mounted in high density on the alumina substrate 1 by means of thin film forming technique and wire bonding of semiconductor element, and the surface mounting type electronic circuit unit that is suitable for miniaturization is realized. Furthermore, some of the capacitors C1 to C7 are formed in non-rectangular configuration having rectangles projected from one side of another rectangle. As the result, the capacitor having desired capacitance value is mounted in high density within a limited space on the alumina substrate 1, and the electronic circuit unit can be further miniaturized thereby.

The case in which some of a plurality of thin film capacitors are formed non-rectangular is described in the above-mentioned embodiment, however, the case in which all the plurality of thin film capacitors are formed non-rectangular or the case in which only one capacitor is formed non-rectangular may be employed depending on the layout of the circuit component parts.

The capacitor C6 disposed between the emitter electrode and the ground electrode of the transistor Tr1

among the thin film capacitors C1 to C7 formed on the alumina substrate 1 comprises two ground capacitors, the one electrode of each of the ground capacitors is connected to the ground conducting pattern P, and the other electrode of each of the ground capacitors is connected to the connection land SL wire-bonded to the emitter electrode of the transistor Tr1 through the conducting patterns P that are separated from each other. As the result, the inductance of the whole conducting pattern to which the two ground capacitors of the capacitor C6 is to be connected is reduced, and the grounding effect of the connection land brought about by the ground capacitor is improved. Furthermore, the parasitic oscillation frequency caused from interaction between the ground capacitors and conducting patterns becomes high, and oscillation at the frequency other than predetermined oscillation frequency is prevented without parasitic oscillation by setting the parasitic oscillation frequency to a value equal to or higher than the operating point frequency of the transistor. Furthermore, because the ground capacitors of the capacitor C6 are different from each other in size, the limited space on the alumina substrate 1 is can be used effectively to bring about the extended layout freedom of the conducting pattern P, and this structure allows the electronic circuit unit to be further miniaturized.

The present invention is applied as described in the above-mentioned embodiment and exhibits the effect

described hereunder.

Thin film circuit elements including capacitors, resistors, and inductance elements are formed on an alumina substrate by means of thin film forming technique and semiconductor bare chips are fixed on the alumina substrate by means of wire bonding, and at least one capacitor out of the above-mentioned capacitors is formed non-rectangular having rectangles projected from one side of a rectangle. As the result, circuit component elements including capacitors can be mounted in high density on the alumina substrate, and a small-sized electronic circuit unit is realized.

Furthermore, because thin film circuit elements including capacitors, resistors, and inductance elements are formed on the alumina substrate at high precision by means of thin film forming technique and the semiconductor element of the transistor is formed by fixing the bare chip by means of wire bonding, the necessary circuit parts are mounted in high density on the alumina substrate, and the surface mounting type electronic circuit unit that is suitable for miniaturization is realized. Furthermore, the conducting pattern has the connection land connected to the electrode of the transistor, the one electrode of each of the plurality of ground capacitors is connected to the ground conducting pattern, and the other electrode of each of the plurality of ground capacitors is connected to the connection land through the conducting pattern that

are separated each. Thereby, the inductance of the whole conducting pattern that connects the ground capacitors is reduced, and the grounding effect of the connection land brought about by the ground capacitors is improved. Furthermore, because the parasitic oscillation frequency caused from interaction between the ground capacitors and conducting patterns becomes high, the oscillation at the frequency other than the predetermined oscillation frequency is prevented without parasitic oscillation by setting the parasitic oscillation frequency to a value equal to or higher than the parasitic oscillation frequency of the transistor.